

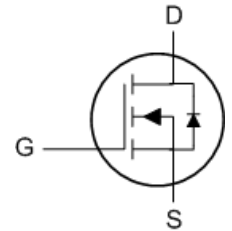
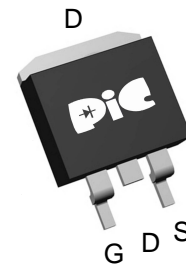
### ➤ General Description

This PAN30TP18BP N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent  $R_{ds(On)}$  performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

### ➤ Feature

- Super Low Gate Charge
- Green Device Available Excellent
- Cdv/dt effect decline
- Advanced high cell densit Trench
- TO-263-2L package design

### ➤ TO-263-2L



### ➤ Application

- DC-DC Converters
- Power Management
- Analog Switch

### ➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current, $V_{GS} @ 10V_{1,6}$	$I_D @ T_C=25^\circ C$	205	A
Continuous Drain Current, $V_{GS} @ 10V_{1,6}$	$I_D @ T_C=100^\circ C$	145	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	500	A
Single Pulse Avalanche Energy <sup>3</sup>	EAS	246	mJ
Avalanche Current	$I_{AS}$	70.2	A
Total Power Dissipation <sup>4</sup>	$P_D @ T_C=25^\circ C$	187	W
Storage Temperature Range	$T_{STG}$	-55 to 175	$^\circ C$
Operating Junction Temperature Range	$T_J$	-55 to 175	$^\circ C$
Thermal Resistance Junction-Ambient <sup>1</sup>	$R_{\theta JA}$	62	$^\circ C/W$
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	0.8	$^\circ C/W$

### ➤ Electrical Characteristics ( $T_J=25^\circ C$ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$BV_{DSS}$ Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to $25^\circ C, I_D=1mA$	---	0.014	---	$V/^\circ C$
Static Drain-Source On-Resistance <sup>2</sup>	$R_{DS(ON)}$	$V_{GS}=10V, I_D=30A$	---	2	---	m $\Omega$
		$V_{GS}=4.5V, I_D=15A$	---	2.6	---	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.5	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		---	-4	---	mV/ $^\circ C$
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ C$	---	---	1	$\mu A$
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ C$	---	---	5	
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
Forward Transconductance	$g_{fs}$	$V_{DS}=5V, I_D=30A$	---	50	---	S
Gate Resistance	$R_g$	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	1.7	---	$\Omega$
Total Gate Charge (4.5V)	$Q_g$	$V_{DS}=15V, V_{GS}=10V, I_D=15A$	---	56.9	---	nC
Gate-Source Charge	$Q_{gs}$		---	13.8	---	
Gate-Drain Charge	$Q_{gd}$		---	23.5	---	
Turn-On Delay Time	$T_{d(on)}$	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega, I_D=1A$	---	20.1	---	ns
Rise Time	$T_r$		---	6.3	---	
Turn-Off Delay Time	$T_{d(off)}$		---	124.6	---	
Fall Time	$T_f$		---	15.8	---	
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	5850	---	pF
Output Capacitance	$C_{oss}$		---	720	---	
Reverse Transfer Capacitance	$C_{rss}$		---	525	---	

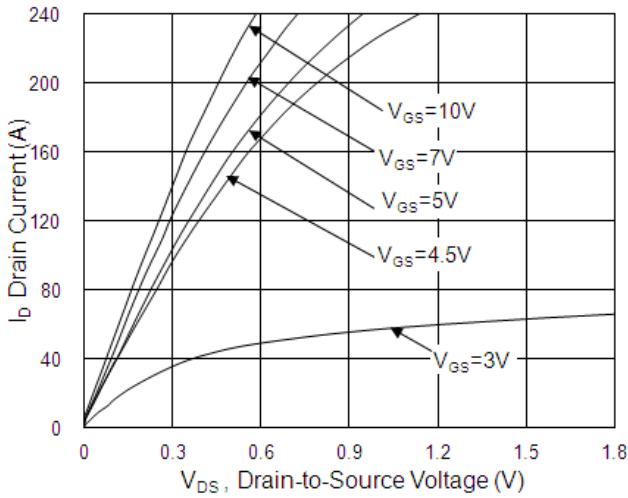
### ➤ Diode Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current <sup>1,5</sup>	$I_S$	$V_G=V_D=0V, \text{Force Current}$	---	---	205	A
Pulsed Source Current <sup>2,5</sup>	$I_{SM}$		---	---	500	A
Diode Forward Voltage <sup>2</sup>	$V_{SD}$	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1.2	V

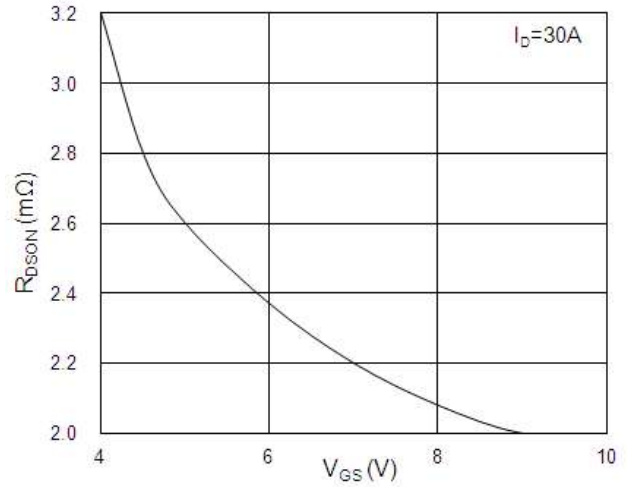
Note :

- 1.Pulse width limited by maximum junction temperature.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=70.2A$
- 4.Ensure that the channel temperature does not exceed  $150^\circ C$ .
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.
- 6.Package limitation current is 70A.

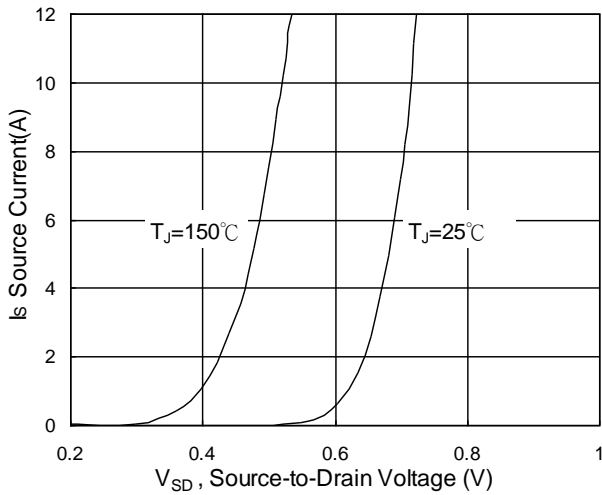
### ➤ Typical Characteristics



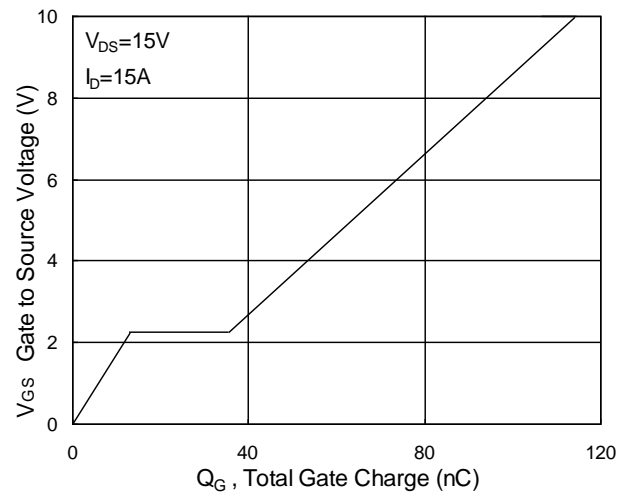
**Fig.1 Typical Output Characteristics**



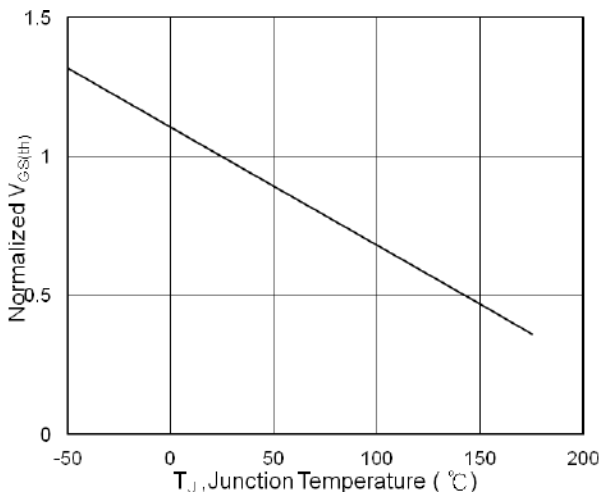
**Fig.2 On-Resistance v.s Gate-Source**



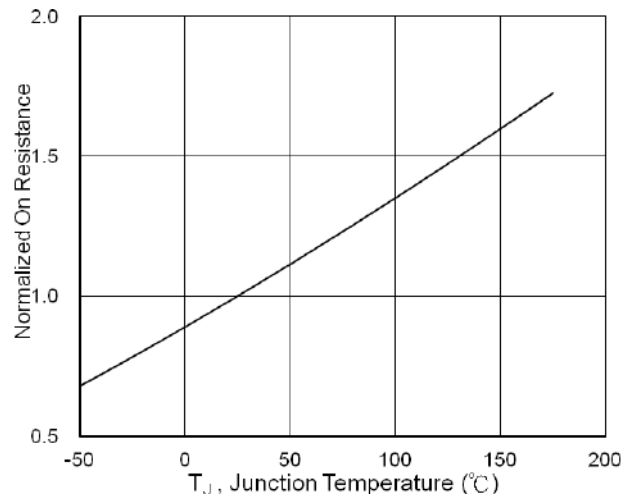
**Fig.3 Forward Characteristics of Reverse**



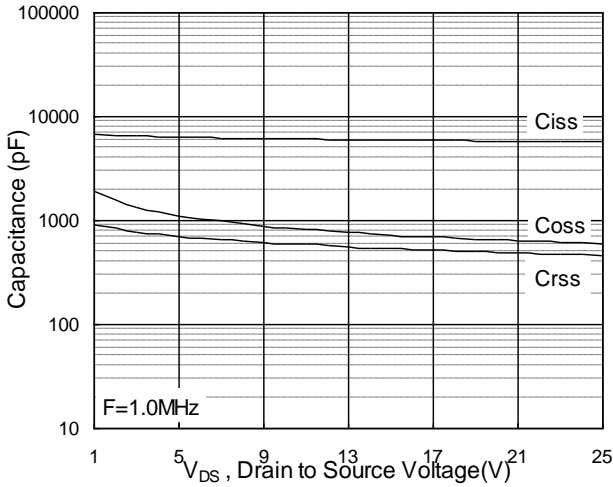
**Fig.4 Gate-Charge Characteristics**



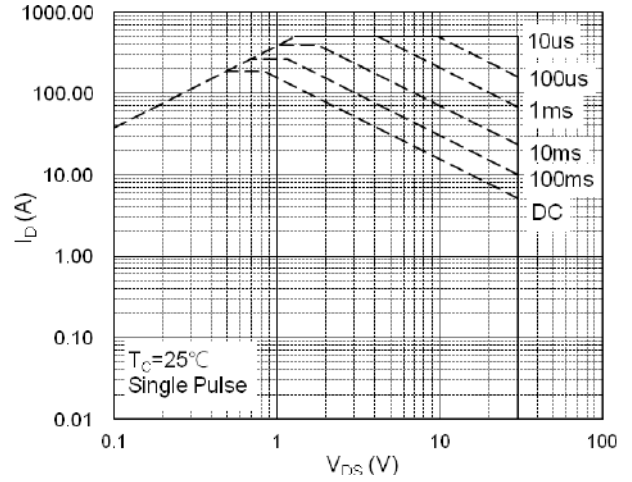
**Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$**



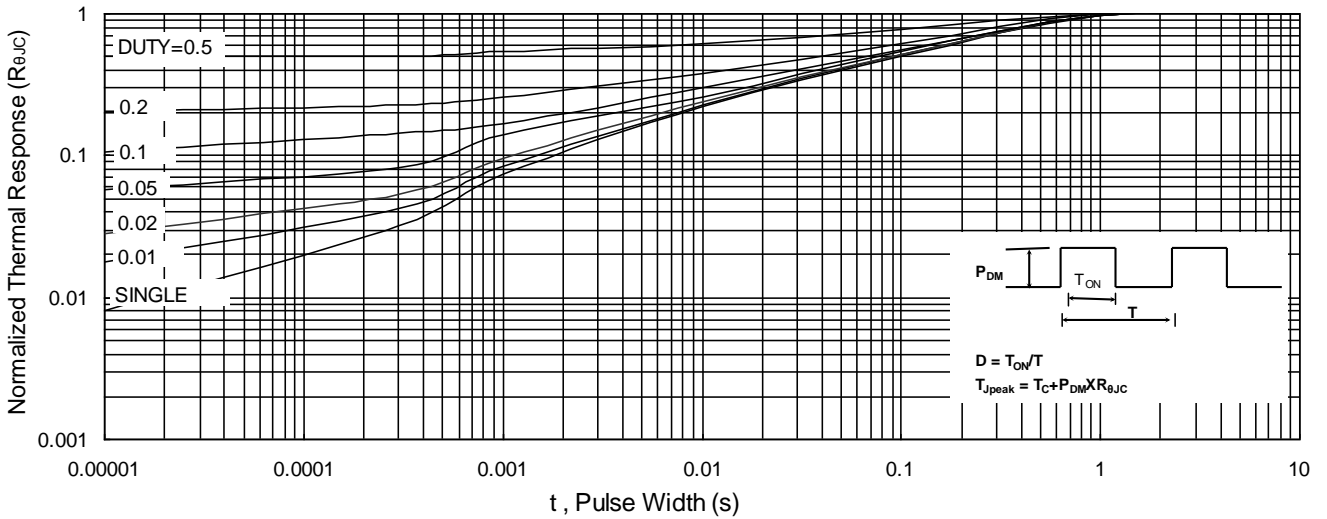
**Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$**



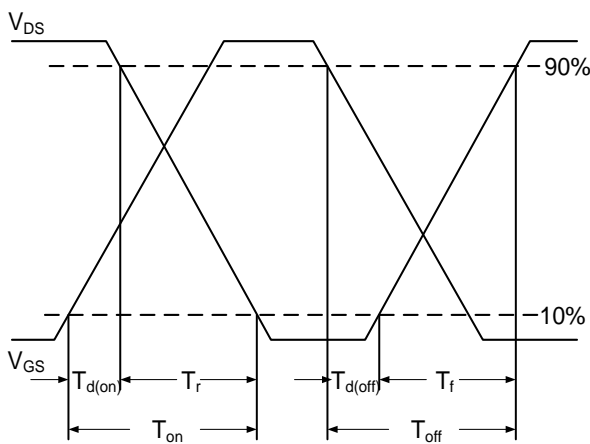
**Fig.7 Capacitance**



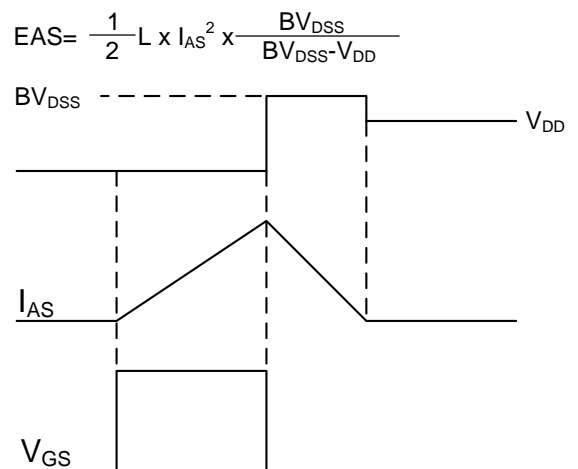
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**

➤ Recommand IR Reflow Soldering Thermal Profile

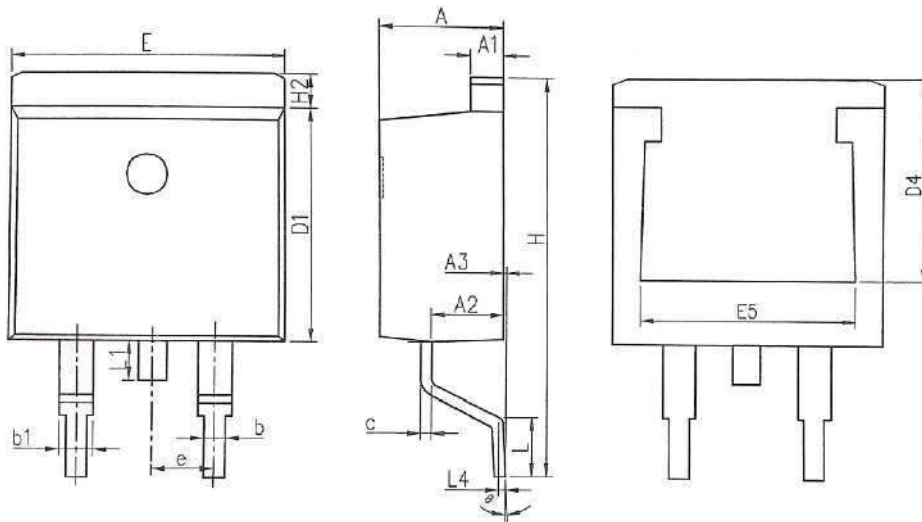


Profile Feature	Pb-Free Assembly Profile
Temperature Min. ( $T_{smin}$ )	150°C
Temperature Max. ( $T_{smax}$ )	200°C
Time ( $t_s$ ) from ( $T_{smin}$ to $T_{smax}$ )	60-120 seconds
Average Ramp-up Rate ( $t_L$ to $t_P$ )	3°C/second max.
Liquidous Temperature ( $T_L$ )	217°C
Time ( $t_L$ ) Maintained Above ( $T_L$ )	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time ( $t_P$ ) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate ( $T_P$ to $T_L$ )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN30TP18BP	TO-263-2L Reel	800

### ➤ Package Information ( TO-263-2L )



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.370	4.770	0.172	0.188
A1	1.220	1.420	0.048	0.056
A2	2.200	2.890	0.087	0.114
A3	0.000	0.250	0.000	0.010
b	0.700	0.960	0.028	0.038
b1	1.170	1.470	0.046	0.058
c	0.300	0.530	0.012	0.021
D1	8.500	9.300	0.335	0.366
D4	6.600	-	0.260	-
E	9.860	10.36	0.388	0.408
E5	7.060	-	0.278	-
e	2.540 BSC		0.100 BSC	
H	14.70	15.70	0.579	0.618
H2	1.070	1.470	0.042	0.058
L	2.000	2.600	0.079	0.102
L1	1.400	1.750	0.055	0.069
L4	0.250 BSC		0.010 BSC	
Θ	0°	9°	0°	9°

Notice.

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